

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
20V	$0.55\Omega @ V_{GS} = 4.5\text{V}$	0.75A
	$0.75\Omega @ V_{GS} = 2.5\text{V}$	0.63A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected up to 1.5kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

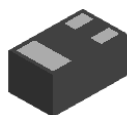
This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

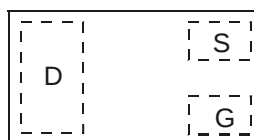
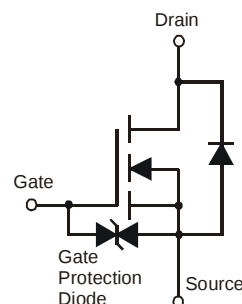
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish — NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 **e4**
- Weight: 0.001 grams (Approximate)

X1-DFN1006-3



Bottom View


 Top View
 Package Pin Configuration


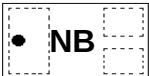
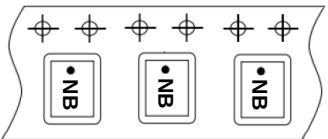
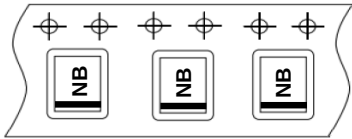
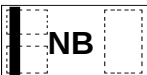
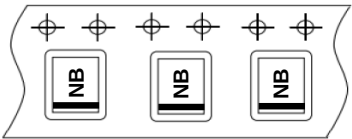
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2400UFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN2400UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

DMN2400UFB-7	 Top View Dot Denotes Drain Side From date code 1527 (YYWW), this changes to:  Top View Bar Denotes Gate and Source Side  
DMN2400UFB-7B	 Top View Bar Denotes Gate and Source Side  NB = Part Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	0.75	A
		T _A = +85°C		0.55	
Continuous Drain Current (Note 5) V _{GS} = 2.5V	Steady State	T _A = +25°C	I _D	0.63	A
		T _A = +85°C		0.45	
Pulsed Drain Current (Note 6)			I _{DM}	3	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.47	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	258	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	100	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±50	μA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.5	-	0.9	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	-	0.55	Ω	V _{GS} = 4.5V, I _D = 600mA
		-	-	0.75		V _{GS} = 2.5V, I _D = 500mA
		-	-	0.9		V _{GS} = 1.8V, I _D = 350mA
Forward Transfer Admittance	Y _{fs}	-	1.0	-	S	V _{DS} = 10V, I _D = 400mA
Diode Forward Voltage (Note 7)	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	36.0	-	pF	V _{DS} = 16V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	5.7	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	4.2	-	pF	
Total Gate Charge	Q _g	-	0.5	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	-	0.07	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.1	-	nC	
Turn-On Delay Time	t _{D(on)}	-	4.11	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _G = 10Ω, I _D = 200mA
Turn-On Rise Time	t _r	-	3.82	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	14.8	-	ns	
Turn-Off Fall Time	t _f	-	9.6	-	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

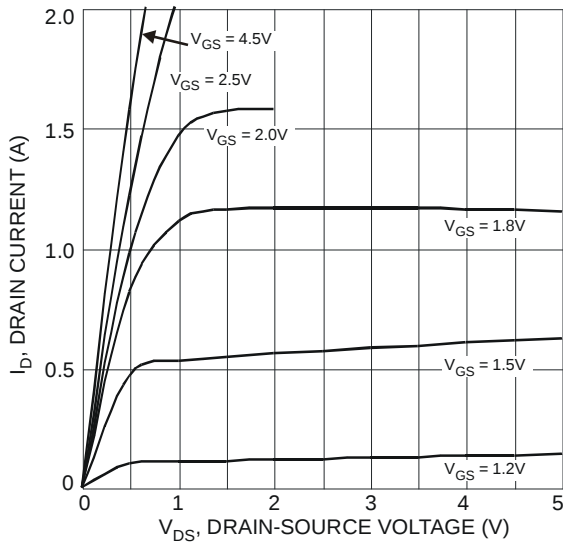


Fig. 1 Typical Output Characteristics

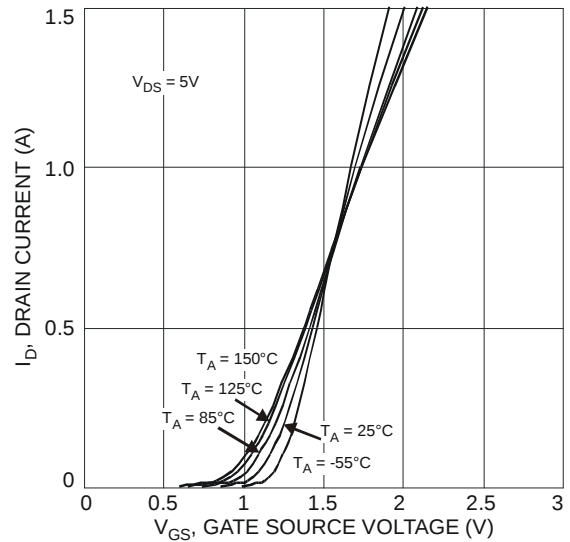


Fig. 2 Typical Transfer Characteristics

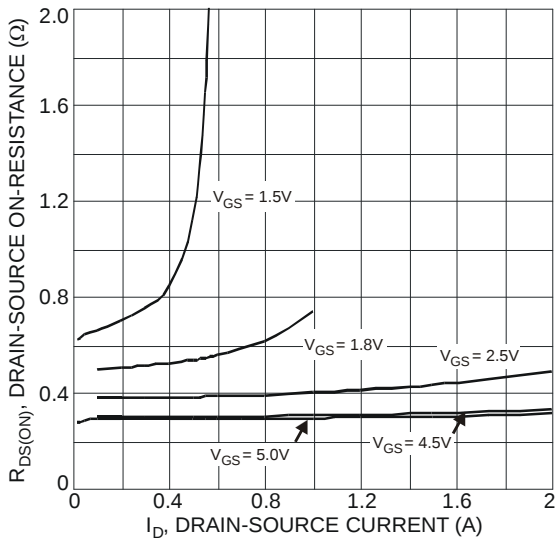


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

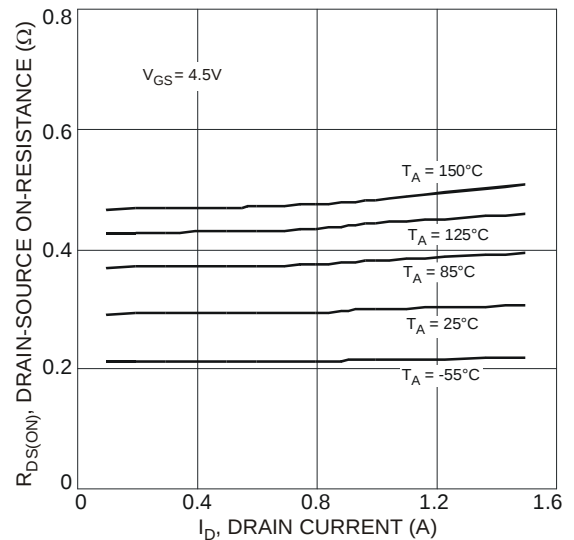


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

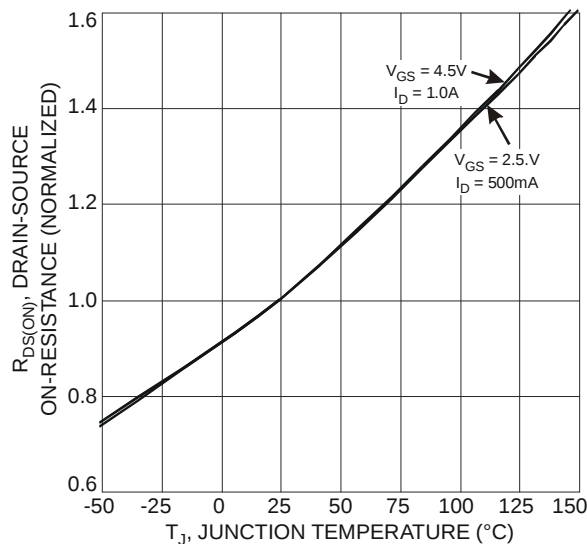


Fig. 5 On-Resistance Variation with Temperature

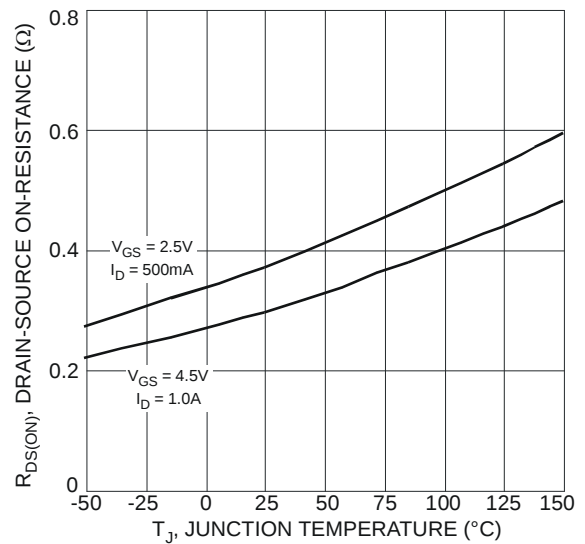


Fig. 6 On-Resistance Variation with Temperature

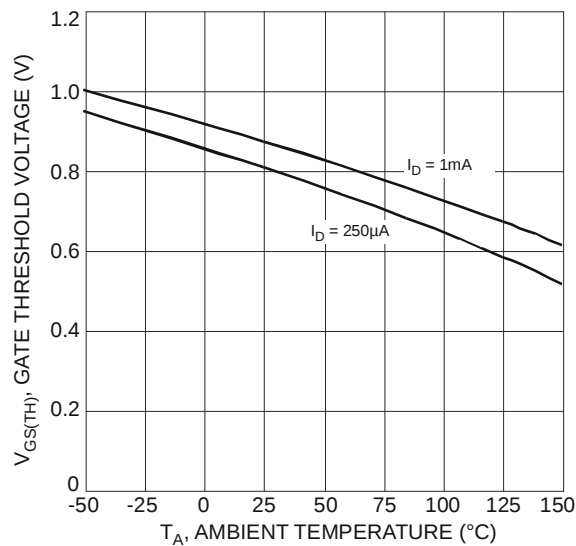


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

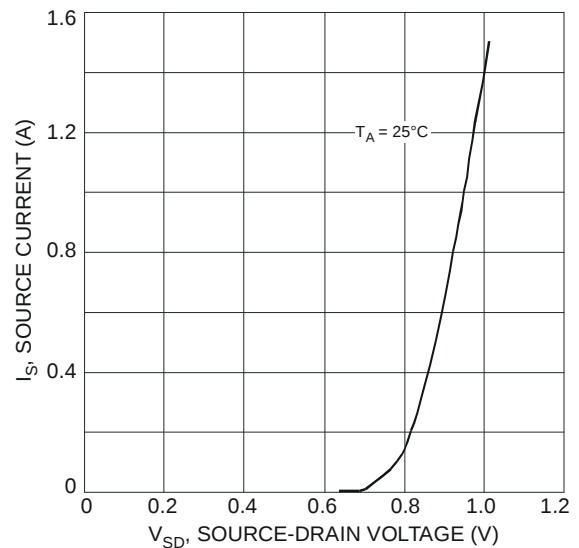


Fig. 8 Diode Forward Voltage vs. Current

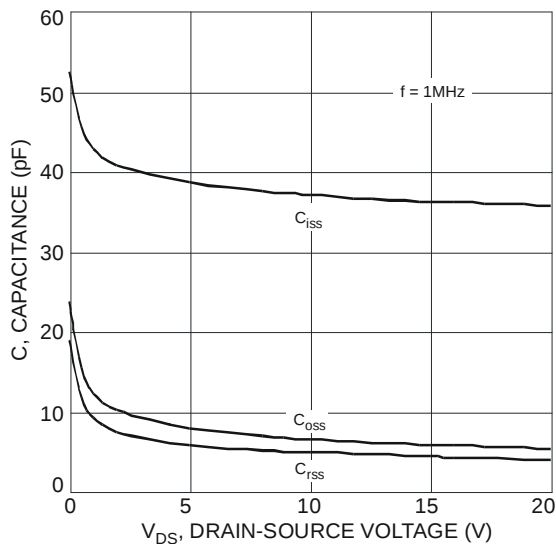


Fig. 9 Typical Capacitance

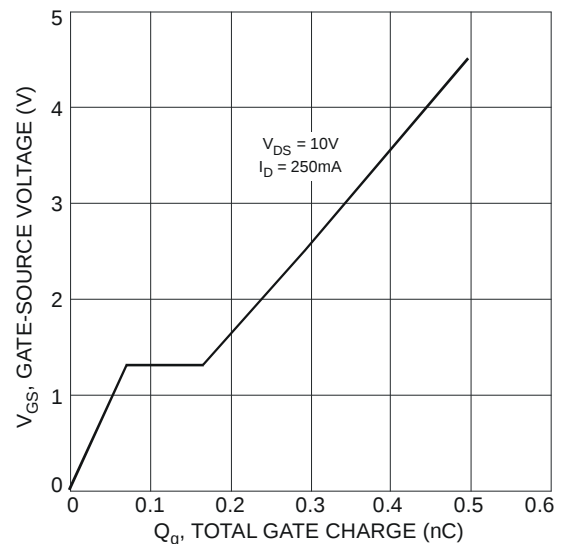


Fig. 10 Gate-Charge Characteristics

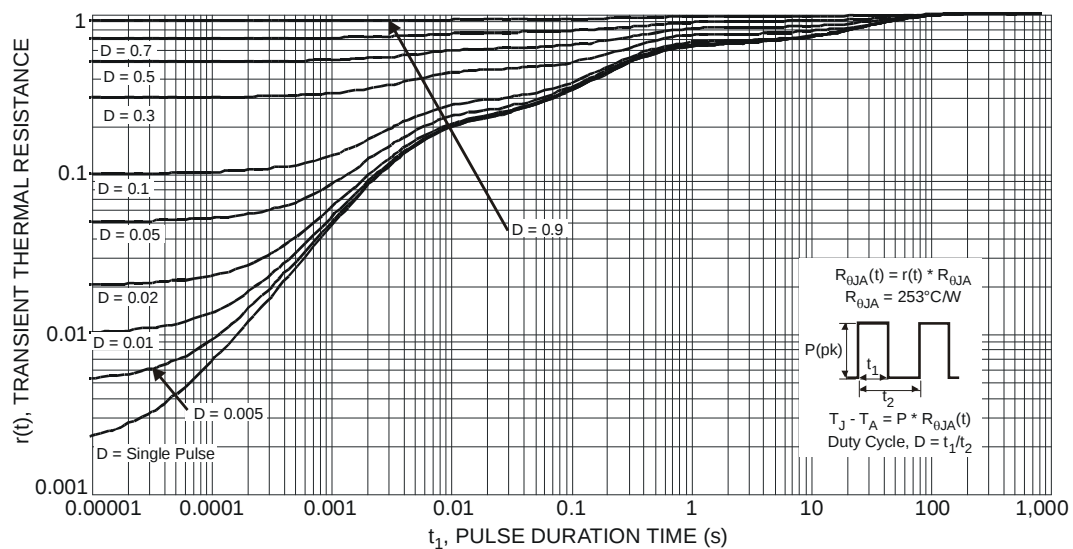
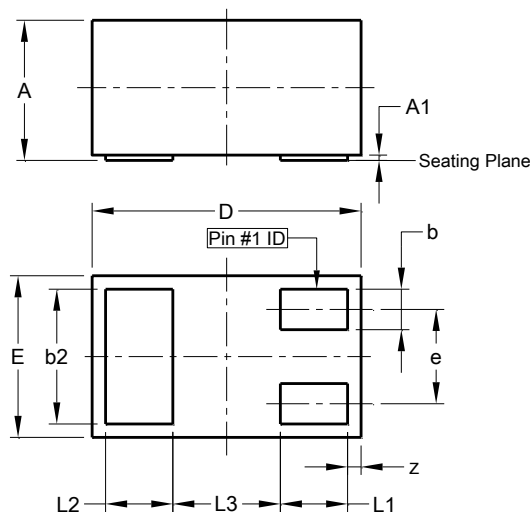


Fig. 11 Transient Thermal Response

Package Outline Dimensions

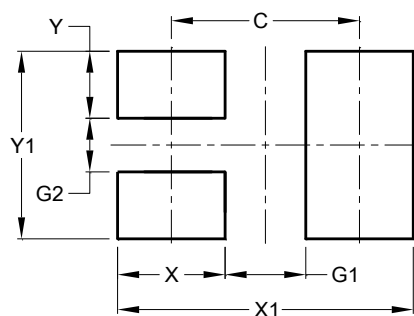
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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